

# Single N-channel MOSFET

ELM14466AA-N

## General description

ELM14466AA-N uses advanced trench technology to provide excellent  $R_{ds(on)}$ , low gate charge and low gate resistance.

## Features

- $V_{ds}=30V$
- $I_d=9.4A$  ( $V_{gs}=10V$ )
- $R_{ds(on)} < 23m\Omega$  ( $V_{gs}=10V$ )
- $R_{ds(on)} < 35m\Omega$  ( $V_{gs}=4.5V$ )

## Maximum absolute ratings

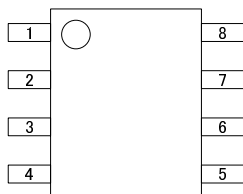
Parameter	Symbol	Limit	Unit	Note	
Drain-source voltage	$V_{ds}$	30	V		
Gate-source voltage	$V_{gs}$	$\pm 20$	V		
Continuous drain current	$I_d$	$T_a=25^\circ C$	9.4	A	1
		$T_a=70^\circ C$	7.7		
Pulsed drain current	$I_{dm}$	50	A	2	
Power dissipation	$P_d$	$T_a=25^\circ C$	3.1	W	
		$T_a=70^\circ C$	2.1		
Junction and storage temperature range	$T_j, T_{stg}$	-55 to 150	$^\circ C$		

## Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$t \leq 10s$	$R\theta_{ja}$	34	40	$^\circ C/W$	1
Maximum junction-to-ambient	Steady-state		62	75	$^\circ C/W$	
Maximum junction-to-lead	Steady-state	$R\theta_{jl}$	18	24	$^\circ C/W$	3

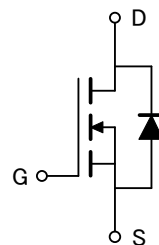
## Pin configuration

SOP-8 (TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

## Circuit



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## Electrical characteristics

T<sub>a</sub>=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-source breakdown voltage	BV <sub>dss</sub>	I <sub>d</sub> =250 μA, V <sub>gs</sub> =0V	30			V
Zero gate voltage drain current	I <sub>dss</sub>	V <sub>ds</sub> =24V V <sub>gs</sub> =0V T <sub>j</sub> =55°C		0.004	1.000 5.000	μA
Gate-body leakage current	I <sub>gss</sub>	V <sub>ds</sub> =0V, V <sub>gs</sub> =±20V			100	nA
Gate threshold voltage	V <sub>gs(th)</sub>	V <sub>ds</sub> =V <sub>gs</sub> , I <sub>d</sub> =250 μA	1.0	1.6	3.0	V
On state drain current	I <sub>d(on)</sub>	V <sub>gs</sub> =4.5V, V <sub>ds</sub> =5V	20			A
Static drain-source on-resistance	R <sub>ds(on)</sub>	V <sub>gs</sub> =10V I <sub>d</sub> =9.4A T <sub>j</sub> =125°C		17	23	mΩ
				24	30	
		V <sub>gs</sub> =4.5V, I <sub>d</sub> =5A		27	35	mΩ
Forward transconductance	G <sub>fs</sub>	V <sub>ds</sub> =5V, I <sub>d</sub> =9.4A	10	24		S
Diode forward voltage	V <sub>sd</sub>	I <sub>s</sub> =1A, V <sub>gs</sub> =0V		0.75	1.00	V
Max. body-diode continuous current	I <sub>s</sub>				4.3	A
<b>DYNAMIC PARAMETERS</b>						
Input capacitance	C <sub>iss</sub>	V <sub>gs</sub> =0V, V <sub>ds</sub> =15V, f=1MHz		621	820	pF
Output capacitance	C <sub>oss</sub>			118		pF
Reverse transfer capacitance	C <sub>rss</sub>			85		pF
Gate resistance	R <sub>g</sub>	V <sub>gs</sub> =0V, V <sub>ds</sub> =0V, f=1MHz		0.8	1.5	Ω
<b>SWITCHING PARAMETERS</b>						
Total gate charge (10V)	Q <sub>g</sub>	V <sub>gs</sub> =10V, V <sub>ds</sub> =15V, I <sub>d</sub> =9.4A		11.3	17.0	nC
Total gate charge (4.5V)	Q <sub>g</sub>			5.7	8.0	nC
Gate-source charge	Q <sub>gs</sub>			2.1		nC
Gate-drain charge	Q <sub>gd</sub>			3.0		nC
Turn-on delay time	t <sub>d(on)</sub>			4.5	6.5	ns
Turn-on rise time	t <sub>r</sub>	V <sub>gs</sub> =10V, V <sub>ds</sub> =15V		3.1	5.0	ns
Turn-off delay time	t <sub>d(off)</sub>	R <sub>L</sub> =1.6 Ω, R <sub>gen</sub> =3 Ω		15.1	23.0	ns
Turn-off fall time	t <sub>f</sub>			2.7	5.0	ns
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>f</sub> =9.4A, dI/dt=100A/μs		15.5	21.0	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>f</sub> =9.4A, dI/dt=100A/μs		7.1	10.0	nC

### NOTE :

1. The value of R<sub>θja</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board of 2oz. Copper, in still air environment with T<sub>a</sub>=25°C. The value in any given applications depends on the user's specific board design, The current rating is based on the t ≤ 10s thermal resistance rating.
2. Repetitive rating, pulse width limited by junction temperature.
3. The R<sub>θja</sub> is the sum of the thermal impedance from junction to lead R<sub>θjl</sub> and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5%max.
5. These tests are performed with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25°C. The SOA curve provides a single pulse rating.

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## Typical electrical and thermal characteristics

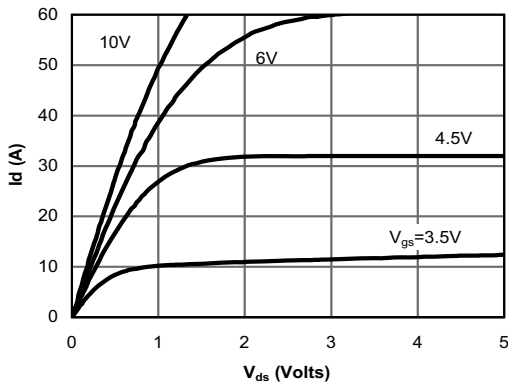


Fig 1: On-Region Characteristics

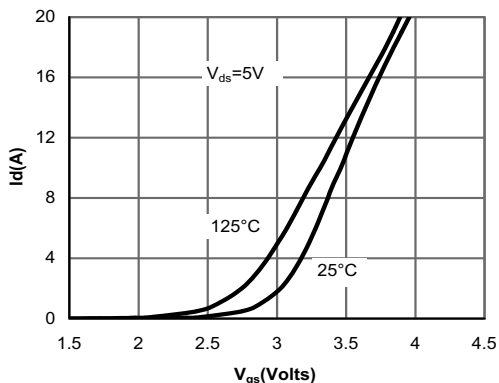


Figure 2: Transfer Characteristics

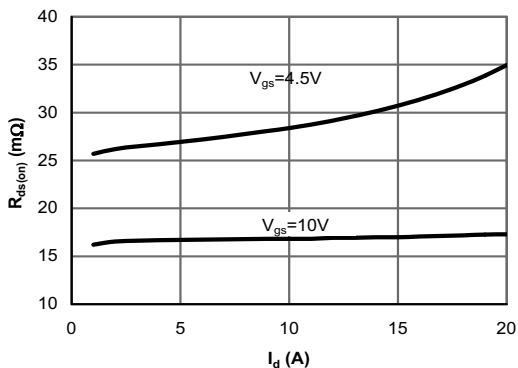


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

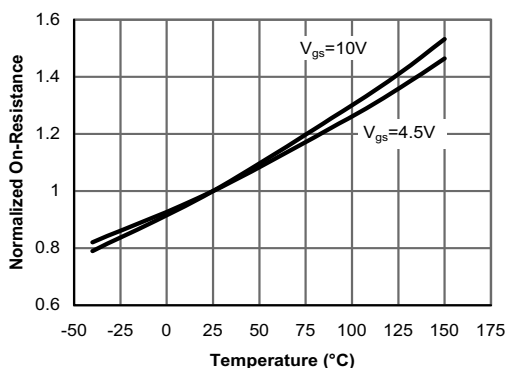


Figure 4: On-Resistance vs. Junction Temperature

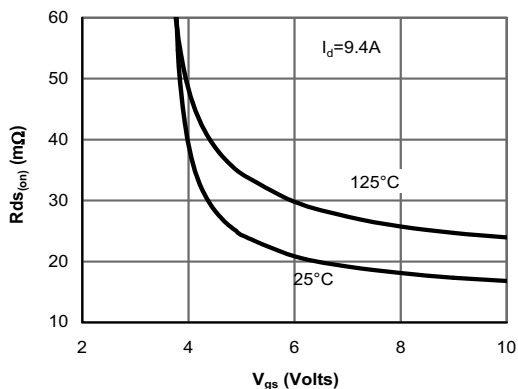


Figure 5: On-Resistance vs. Gate-Source Voltage

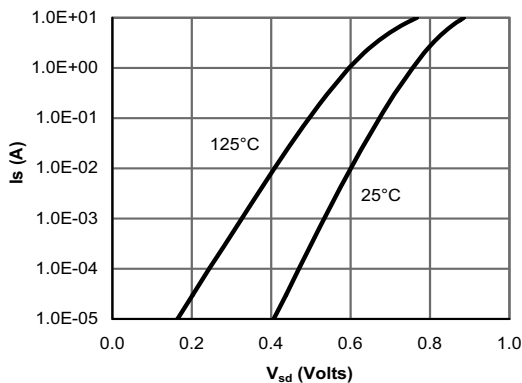


Figure 6: Body-Diode Characteristics

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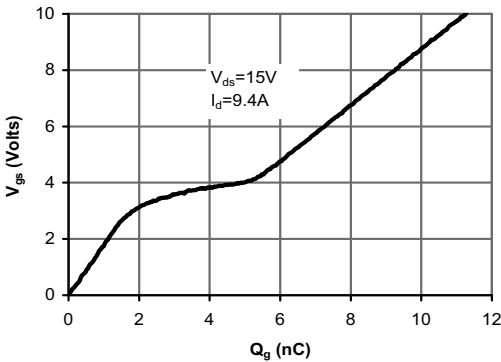


Figure 7: Gate-Charge Characteristics

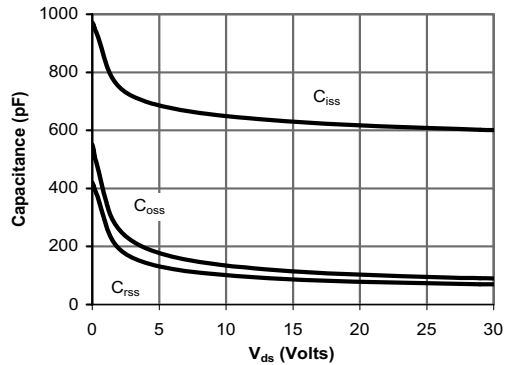


Figure 8: Capacitance Characteristics

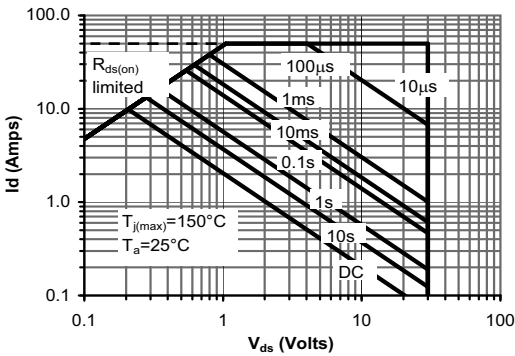


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

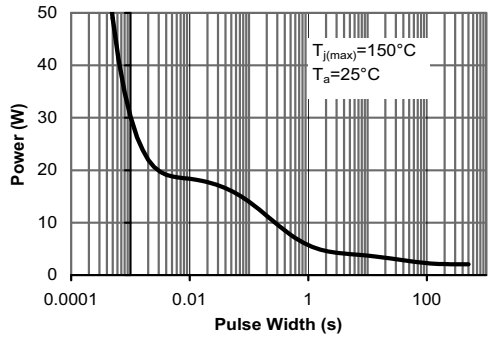


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

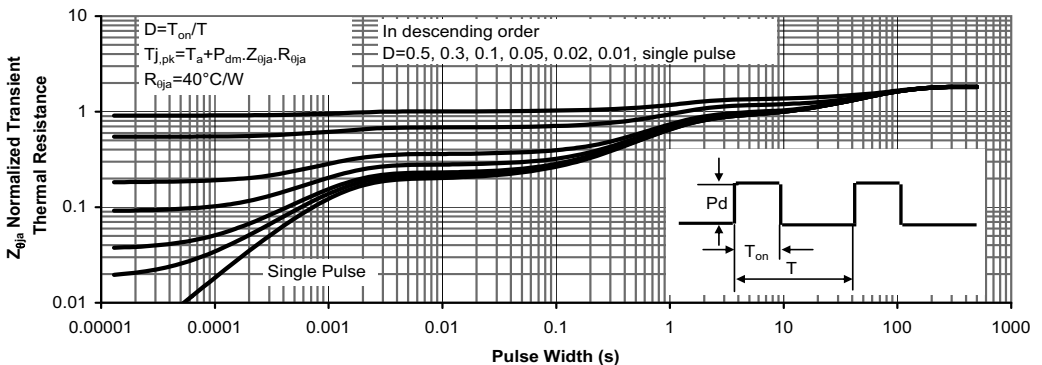


Figure 11: Normalized Maximum Transient Thermal Impedance